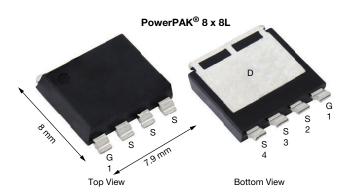


Vishay Siliconix

Automotive N-Channel 100 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY			
V _{DS} (V)	100		
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0055		
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.0062		
I _D (A) ^e	136		
Configuration	Single		

FEATURES

- TrenchFET® Gen IV power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Thin 1.9 mm height
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



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G O	7
N-Channel MOSFET	5

ORDERING INFORMATION	
Package	PowerPAK 8 x 8L
Lead (Pb)-free and halogen-free	SQJQ114EL (for detailed order number please see www.vishay.com/doc?79776)

ABSOLUTE MAXIMUM RATING	GS (1C = 25 °C, unless	otherwise noted	')	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V_{DS}	100	V
Gate-source voltage		V_{GS}	± 20	V
Continuous drain current e	T _C = 25 °C	1	136	
	T _C = 125 °C	l _D	78	
Continuous source current (diode conduction) e		I _S	252	Α
Pulsed drain current a, e		I _{DM}	311	
Single pulse avalanche current	L = 0.1 mH	I _{AS}	46	
Single pulse avalanche energy	L = U.1 IIIH	E _{AS}	105	mJ
Maximum power dissipation ^e	T _C = 25 °C	D	277	10/
	T _C = 125 °C	P_{D}	92	W
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	00
Soldering recommendations (peak temperature) c		· ·	260	°C

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-ambient	PCB mount b	R_{thJA}	44	°C/W	
Junction-to-case (drain) ^d		R _{thJC}	0.54	C/VV	

Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- b. When mounted on 1" square PCB (FR4 material)
- c. See solder profile (www.vishay.com/doc?73257)
- d. As per JESD51-14
- e. Values based on RthJC and TC of 25 °C. Actual values achievable will be dependent on the thermal characteristics of the complete system



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static						•	
Drain-source breakdown voltage	V_{DS}	V _{GS} = 0, I _D = 250 μA		100	-	-	V
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$		1.4	1.9	2.4	V
Gate-source leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA
		V _{GS} = 0 V	V _{DS} = 100 V	-	-	1	μA
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 100 V, T _J = 125 °C	-	-	50	
		$V_{GS} = 0 V$	V _{DS} = 100 V, T _J = 175 °C	-		500	
On-state drain current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	50		-	Α
Drain-source on-state resistance a		V _{GS} = 10 V	I _D = 20 A	-	0.0035	0.0055	Ω
	D	V _{GS} = 10 V	I _D = 20 A, T _J = 125 °C	1	-	0.0120	
	R _{DS(on)}	V _{GS} = 10 V	I _D = 20 A, T _J = 175 °C	-	-	0.0150	
		$V_{GS} = 4.5 \text{ V}$	I _D = 20 A	1	0.0048	0.0062	
Forward transconductance b	9 _{fs}	V_{DS}	= 15 V, I _D = 15 A	1	165	-	S
Dynamic ^b							
Input capacitance	C _{iss}			-	6428	9000	pF
Output capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = 25 V, f = 1 MHz	-	618	866	
Reverse transfer capacitance	C _{rss}	-3 .		1	39	55	1
Total gate charge ^c	Qg		V _{DS} = 50 V, I _D = 20 A	-	102	158	nC
Gate-source charge ^c	Q_{gs}	$V_{GS} = 10 \text{ V}$		-	20	-	
Gate-drain charge ^c	Q_{gd}			-	14	=	
Gate resistance	R_g	f = 1 MHz		0.5	1.1	1.8	Ω
Turn-on delay time ^c	t _{d(on)}				14	22	
Rise time ^c	t _r	$V_{DD} = 50 \text{ V}, \text{ R}_L = 2.5 \Omega,$ $I_D \cong 20 \text{ A}, V_{GEN} = 10 \text{ V}, \text{ R}_g = 1 \Omega$		-	4	8	no
Turn-off delay time ^c	t _{d(off)}			1	47	71	ns
Fall time ^c	t _f			1	6	9	
Source-Drain Diode Ratings and Charac	teristics ^b						
Pulsed current ^a	I _{SM}			-	-	311	Α
Forward voltage	V_{SD}	I _F = 40 A, V _{GS} = 0 V		-	0.7	1.1	V
Body diode reverse recovery time	t _{rr}	I _F = 15 A, di/dt = 100 A/μs		-	49	98	ns
Body diode reverse recovery charge	Q _{rr}			-	91	182	nC
Reverse recovery fall time	ta			-	40	-	
Reverse recovery rise time	t _b			-	10	-	ns
Body diode peak reverse recovery current	I _{RM(REC)}			-	3.4	-	Α
	(1120)				l .	1	1

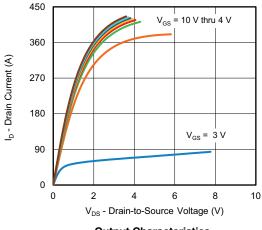
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

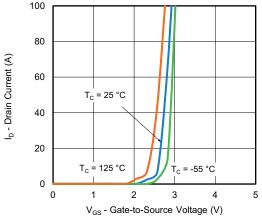
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



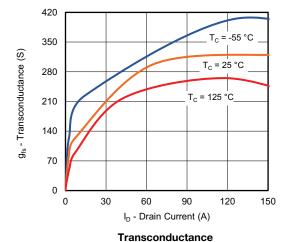
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



Output Characteristics

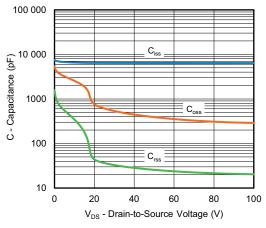


Transfer Characteristics

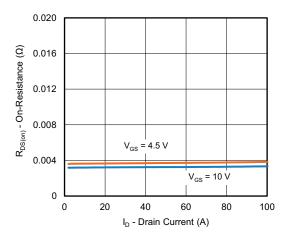


450
360
270
180
T_c = 125 °C
T_c = 25 °C
90
0 2 4 6 8 10
V_{cs} - Gate-to-Source Voltage (V)

Transfer Characteristics



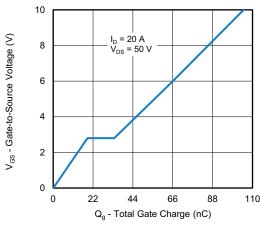
Capacitance



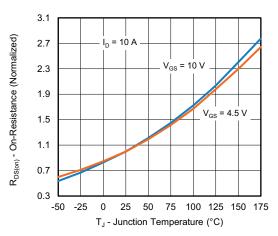
On-Resistance vs. Drain Current



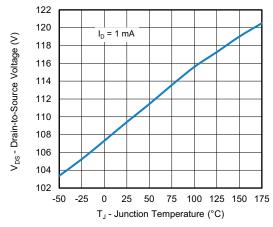
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



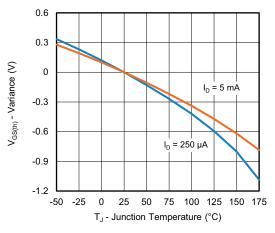
Gate Charge



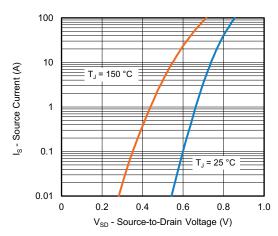
On-Resistance vs. Junction Temperature



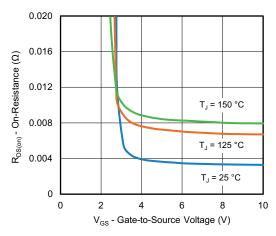
Drain Source Breakdown vs. Junction Temperature



Threshold Voltage



Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

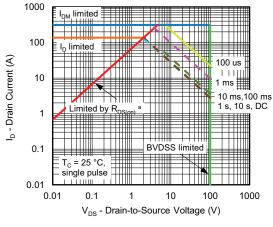
Note

a. V_{GS} > minimum V_{GS} at which R_{DS(on)} is specified

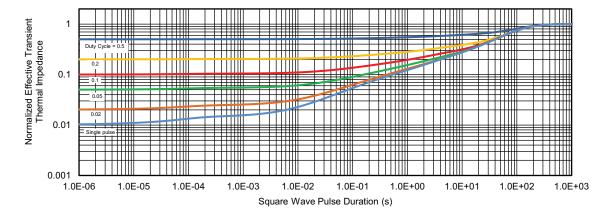
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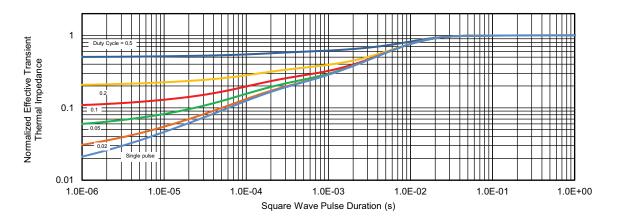
THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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